

L Number	Hits	Search Text	DB	Time stamp
1	5184	transistor and source and drain and (exposing with substrate)	USPAT; US-PGPUB	2004/03/30 10:13
2	174	((transistor and source and drain and (exposing with substrate)) and (implanting same exposing same source))	USPAT; US-PGPUB	2004/03/30 10:12
3	122	((transistor and source and drain and (exposing with substrate)) and (implanting same exposing same source)) and @ad<20020118	USPAT; US-PGPUB	2004/03/30 10:00
4	936	((transistor and source and drain and (exposing with substrate)) and (implanting same source))	USPAT; US-PGPUB	2004/03/30 10:00
5	2	((transistor and source and drain and (exposing with substrate)) and (implanting same source)) and @ad<20020118 and (print adj head)	USPAT; US-PGPUB	2004/03/30 10:13
6	1653	((transistor and source and drain and (exposing with substrate)) and (implanting) and (exposing with substrate))	USPAT; US-PGPUB	2004/03/30 10:29
7	2	((transistor and source and drain and (exposing with substrate)) and (implanting) and (exposing with substrate)) and @ad<20020118 and (print adj head)	USPAT; US-PGPUB	2004/03/30 10:13
8	1374	((transistor and source and drain and (exposing with substrate)) and (implanting) and (exposing with substrate)) and @ad<20020118	USPAT; US-PGPUB	2004/03/30 10:42
9	4	((print adj head) and (implanting) and (exposing with substrate))	USPAT; US-PGPUB	2004/03/30 10:30
10	11	((print adj head) and (implanting same source))	USPAT; US-PGPUB	2004/03/30 10:54
11	7452	((deposited with oxide) and transistor and (implanting))	USPAT; US-PGPUB	2004/03/30 10:48
12	114	((deposited with oxide) and transistor and (implanting)) and (print)	USPAT; US-PGPUB	2004/03/30 10:42
13	97	((deposited with oxide) and transistor and (implanting)) and (print)) and @ad<20020118	USPAT; US-PGPUB	2004/03/30 10:54
14	185	((deposited with oxide) and transistor and (implanting))	EPO; JPO; DERWENT; IBM_TDB	2004/03/30 10:53
17	953	((insulating or insulator) same exposing same substrate) and transistor and (implanting)	USPAT; US-PGPUB	2004/03/30 10:54
19	10	((insulating or insulator) same exposing same substrate) and transistor and (implanting)) and @ad<20020118 ) and print	USPAT; US-PGPUB	2004/03/30 10:54
18	754	((insulating or insulator) same exposing same substrate) and transistor and (implanting)) and @ad<20020118	USPAT; US-PGPUB	2004/03/30 10:56